

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method comprising:  
forming a barrier layer on a substrate surface including in at least one contact opening  
and a field region relative to the contact opening;  
forming an interconnect in the contact opening; and  
reducing the electrical conductivity of the barrier layer in the field region selective of the  
barrier layer in the at least one contact opening.
2. (Original) The method of claim 1, wherein reducing the electrical conductivity comprises oxidizing a material of the barrier layer.
3. (Original) The method of claim 1, wherein the substrate surface comprises a dielectric layer and the contact opening comprises a via through the dielectric layer to a contact point.
4. (Original) The method of claim 3, wherein the contact opening further comprises a trench and forming an interconnect comprises depositing a conductive material in the via and the trench.
5. (Original) The method of claim 4, wherein depositing the conductive material comprises:  
electroplating;  
removing a portion of the conductive material in the contact opening; and  
electroless plating selectively for the conductive material.
6. (Original) The method of claim 5, wherein electroless plating comprises:  
plating a first material; and  
plating a second material on the first material.
7. (Currently Amended) A method comprising:  
forming a barrier layer on a substrate surface including a dielectric layer and a contact opening:

depositing a conductive material in the contact opening;  
removing the conductive material sufficient to expose the barrier layer on the substrate surface; and  
after removing the conductive material, reducing the electrical conductivity of the barrier layer.

8. (Original) The method of claim 7, wherein reducing the electrical conductivity comprises oxidizing a material of the barrier layer.
9. (Original) The method of claim 7, wherein depositing the conductive material comprises:  
electroplating;  
removing a portion of the conductive material in the contact opening; and  
electroless plating selectively for the conductive material.
10. (Original) The method of claim 9, wherein electroless plating comprises:  
plating a first material; and  
plating a second material on the first material.
11. (Original) The method of claim 9, wherein the contact opening comprises a via to a contact point and a trench, and removing a portion of the conductive material comprises removing a portion of the conductive material within the trench.

Claims 12-15 (Canceled)